

Cold ablation driven by localized forces: a femtosecond electron diffraction study

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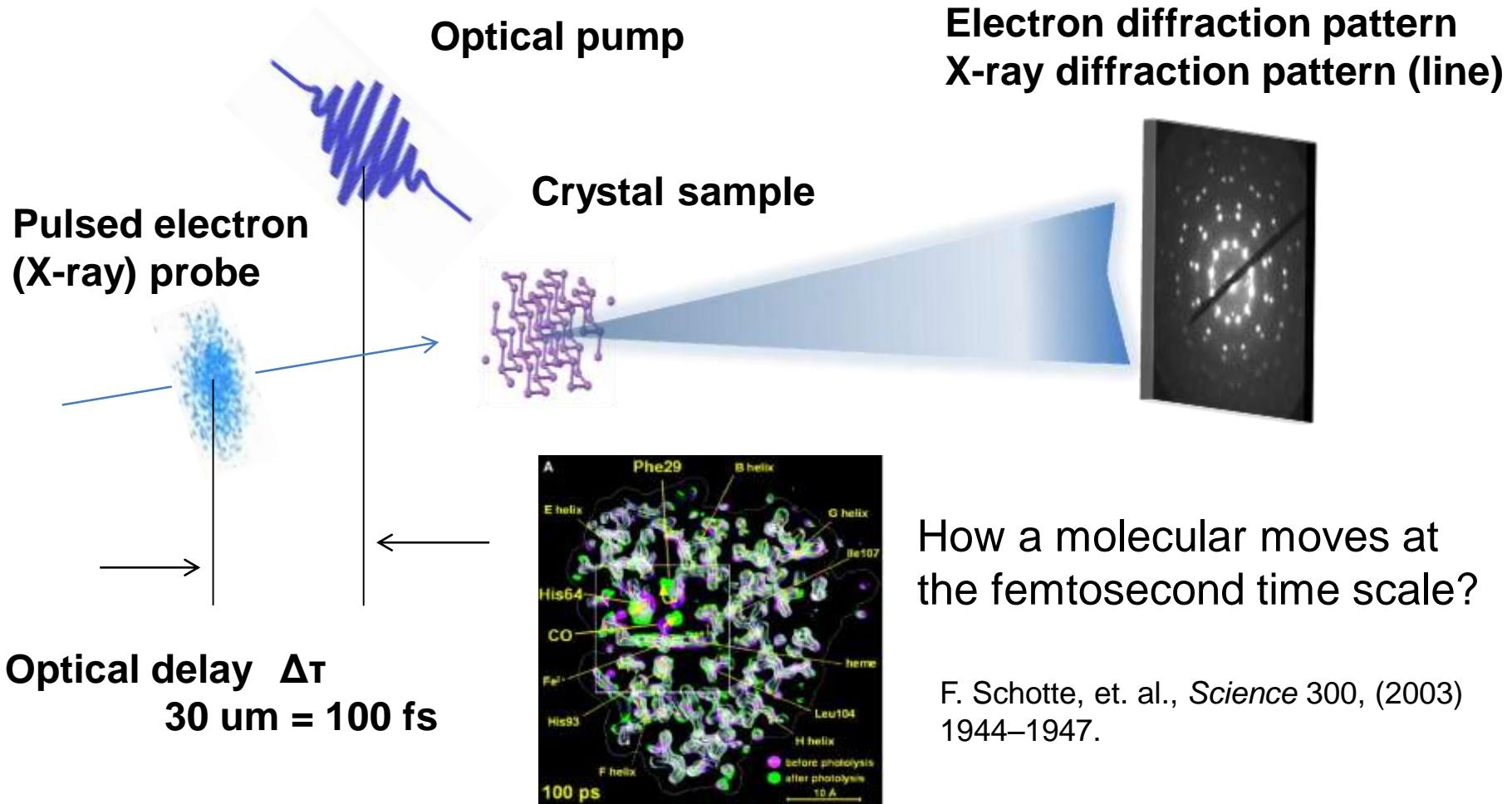
Michał Kochman
Derek Wann
Carole Morrison

Outline

- **Electron diffraction setup**
 - Motivation
 - DC gun, RF gun, Relativistic gun
 - Pulse characterization
- **Science with electron diffraction**
 - Single-shot experiment
 - KI Cold ablation driven by localised forces
 - Multiple-shot experiment
 - Pt(dmit)₂ Coherent phonon in large lattice material

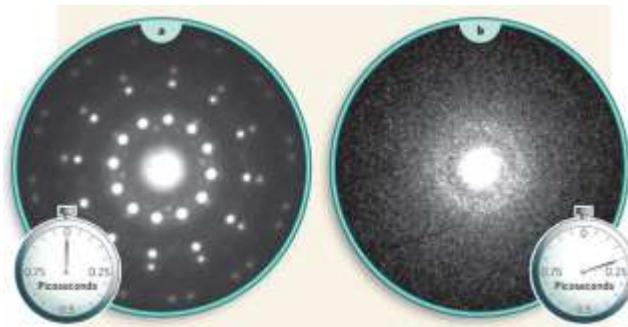
Femtosecond electron diffraction

Optical pump
Electron probe method

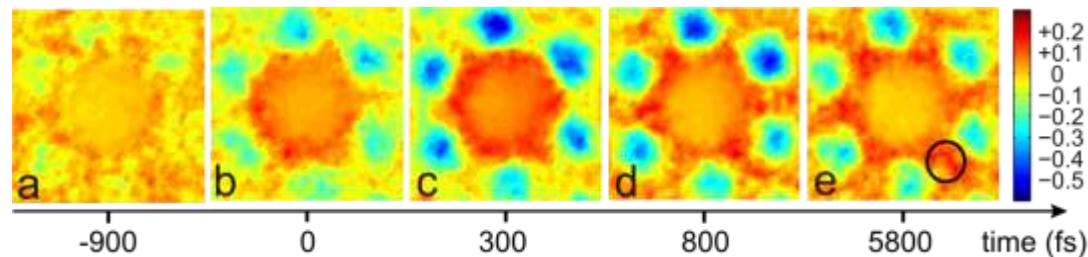


Electron diffraction studies from Toronto

Al, Au, Bi, Si melting



TaS₂ CDW



M. Eichberger et al, Nature **468**, 799 (2010).

G. Scianini et al, Nature **458**, 56 (2009).

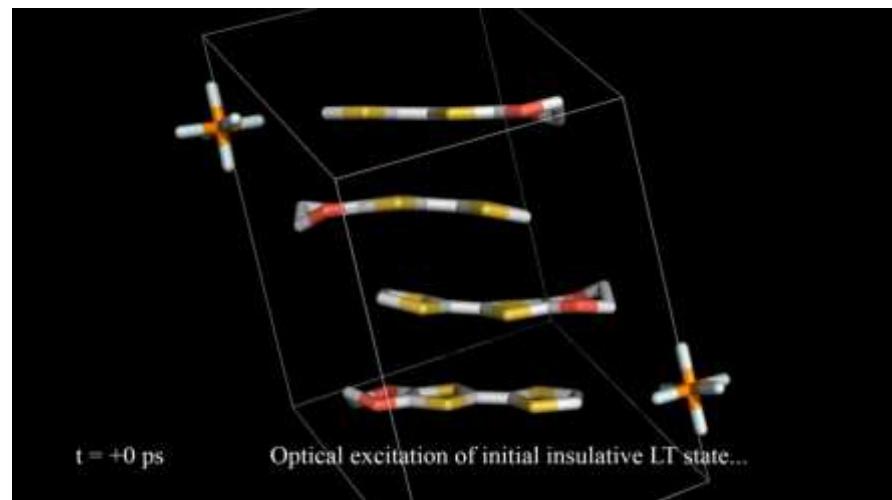
(EDO-TTF)₂ PF₆
Diarylethene

Phase transition

-2000 fs



M. Gao et al, Nature **496**, 343 (2013).



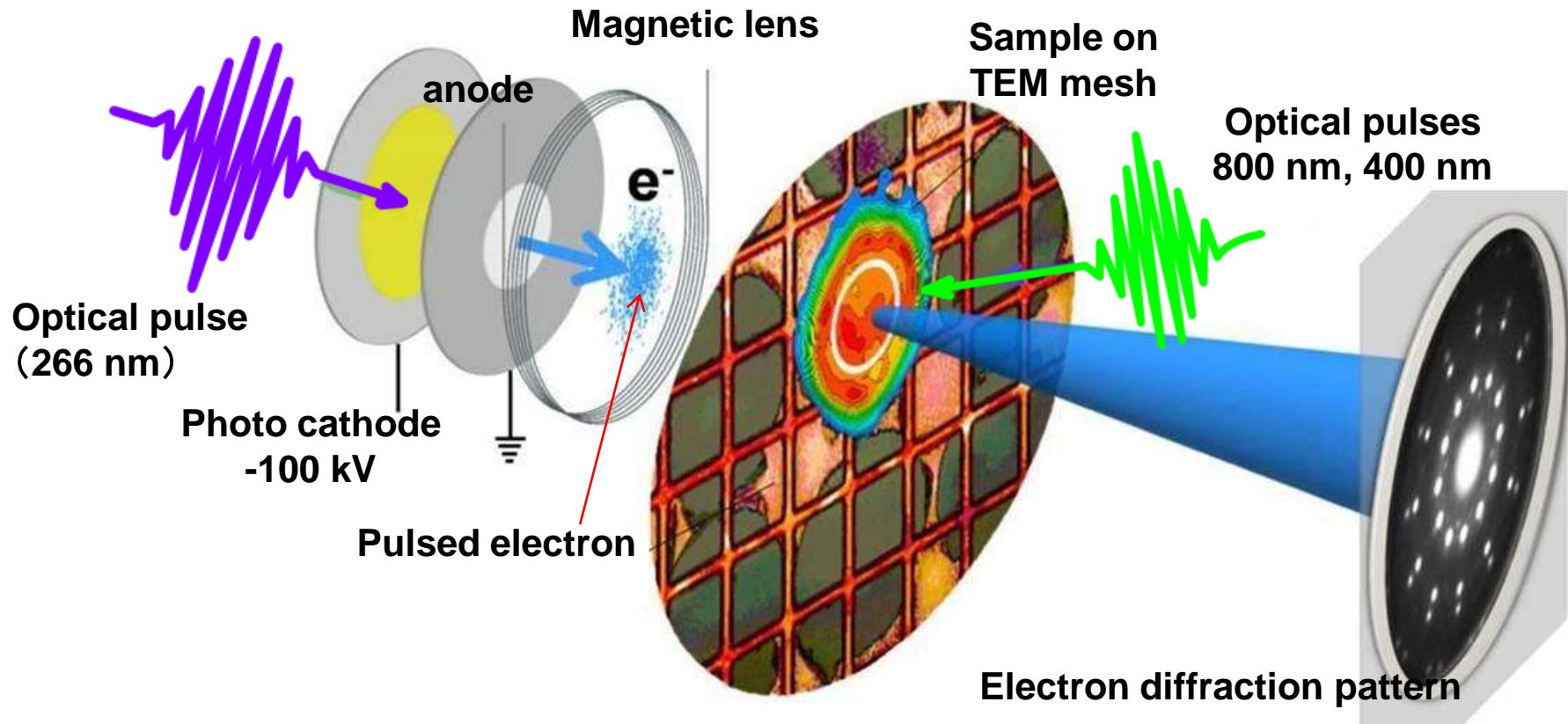
Electron vs X-ray

	Electrons (100 keV)	X-ray (10 keV)
Wavelength [Å]	0.04	1.2
Mechanism of radiation damage	Secondary electron emission	Photoelectric
Ratio (inelastic/elastic) scattering events	3	10
Energy deposited relative electron per elastic event	1	>1000
Elastic mean free path	1	$10^4 - 10^5$
Coherence length	1 – 10 nm	>1 μm

XFEL and Electron gun



DC Femtosecond electron diffraction

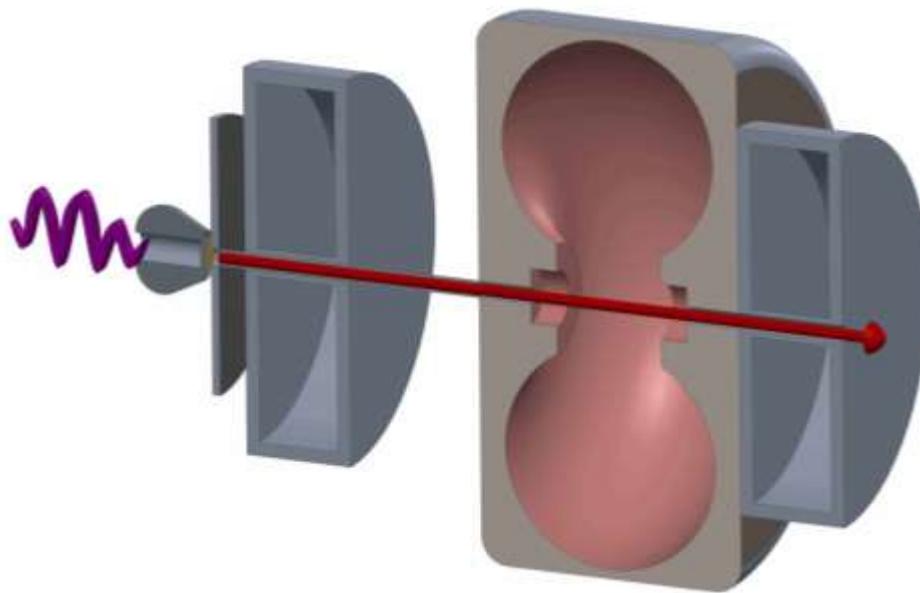


Accel voltage : 90 – 120 kV

Pulse duration : 300 – 500 fs

Electron density : 10^4 – 10^5 electrons/pulse

Femtosecond Electron diffraction + RF



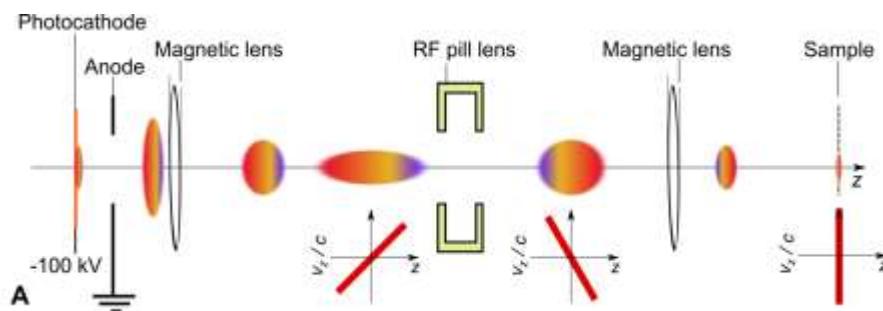
Buncher Machine

100 keV

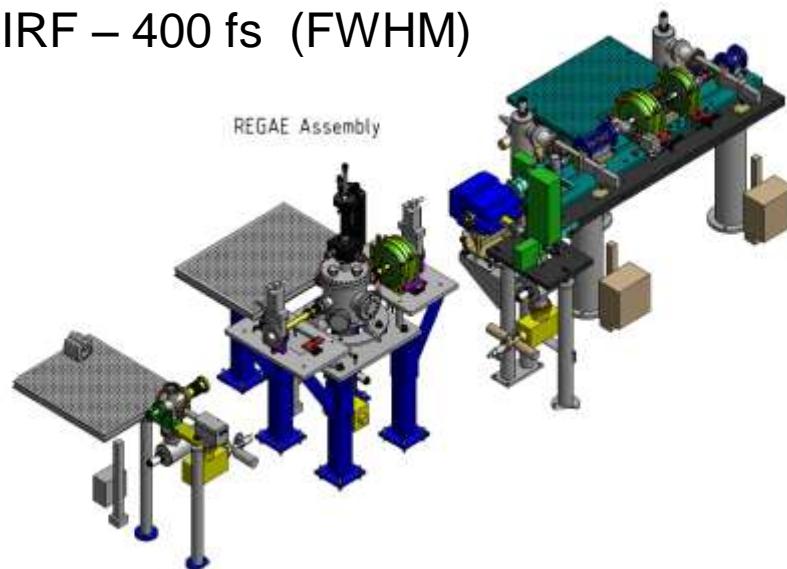
10 Hz

200000 e/pulse

IRF – 400 fs (FWHM)



M. Gao, H. Jean-Ruel et al., Opt. Express **20**, 12048 (2012).



REGAE

3–5 MeV

12.5 Hz

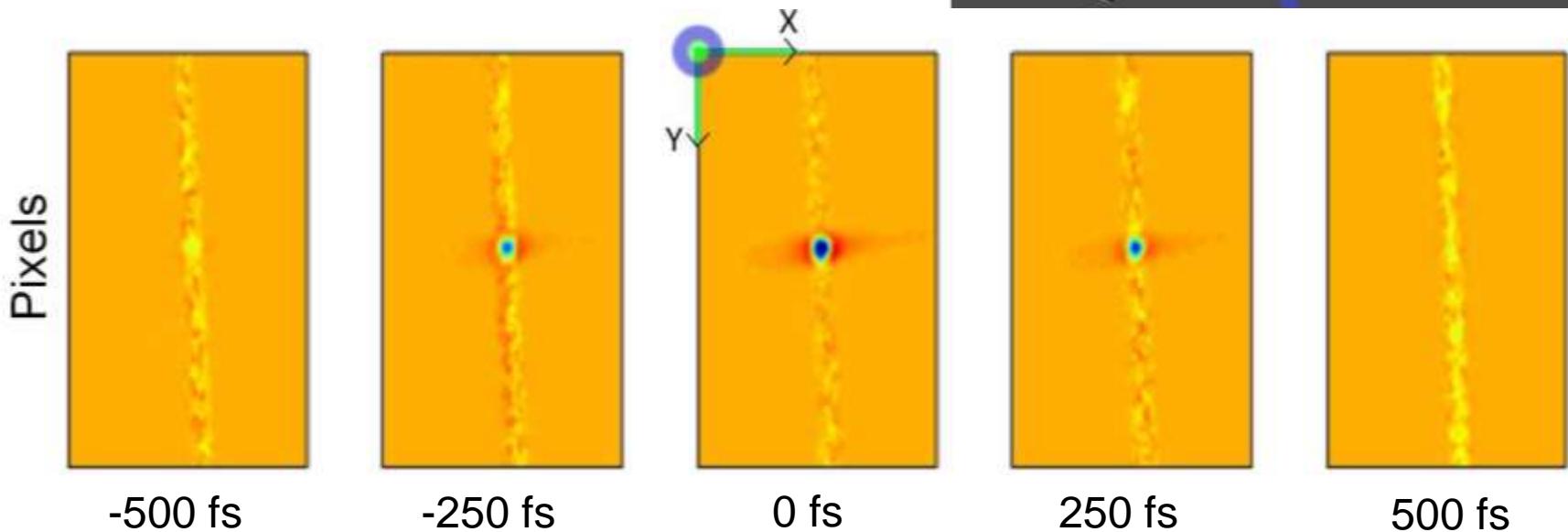
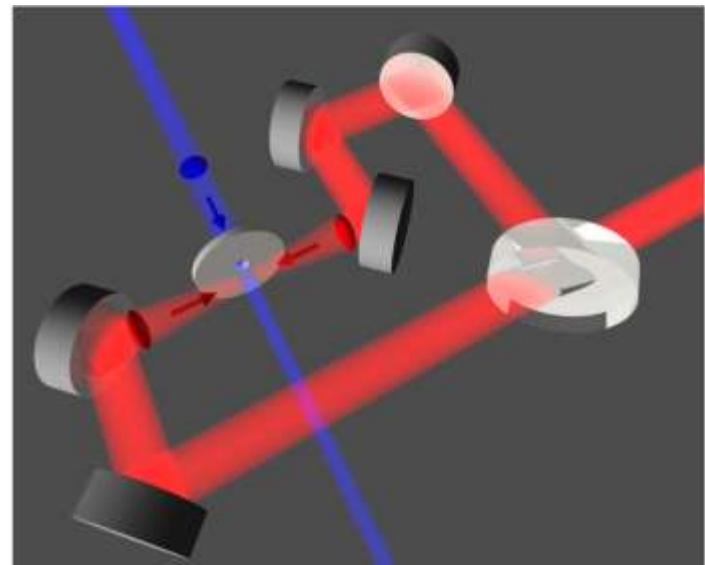
1×10^7 e/pulse

IRF – <50 fs (FWHM)

Pulse characterization Ponderomotive

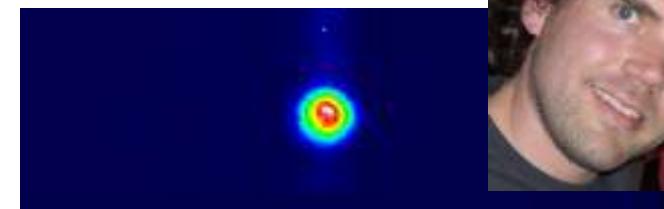
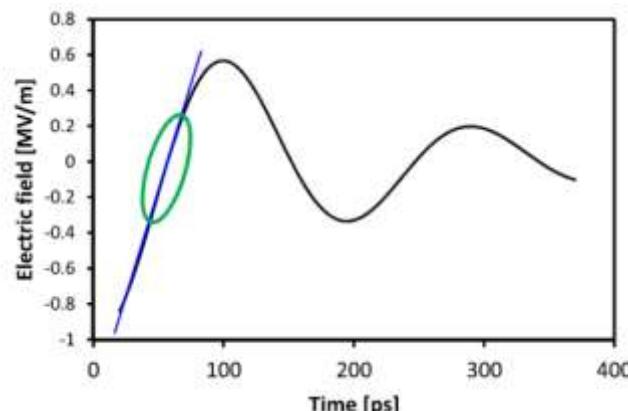
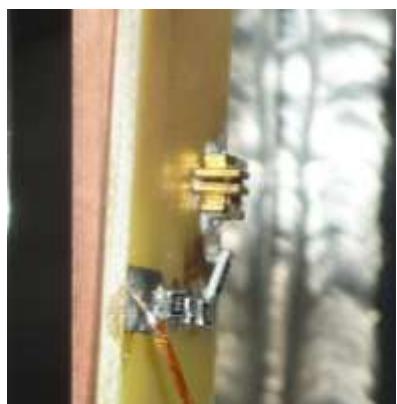
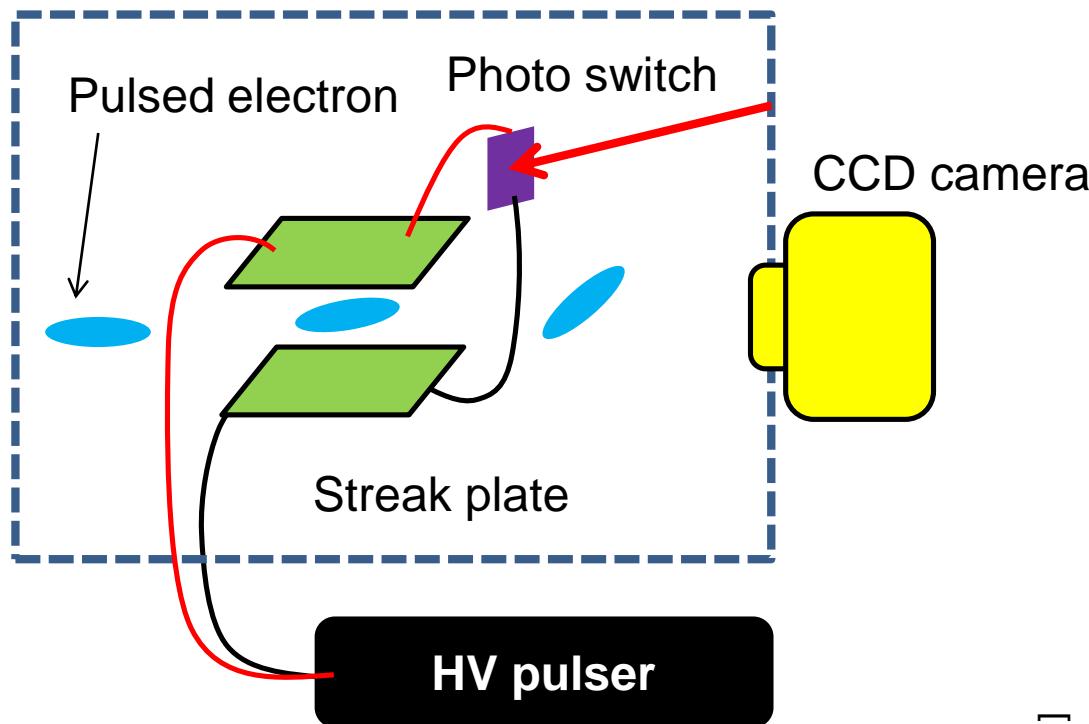
Full characterization of RF compressed femtosecond electron pulses using ponderomotive scattering

Meng Gao,¹ Hubert Jean-Ruel,¹ Ryan R. Cooney,¹ Jonathan Stampe,³
Mark de Jong,³ Maher Harb,^{1,4} German Sciaiani,² Gustavo Moriena,¹
and R. J. Dwayne Miller^{1,2,*}

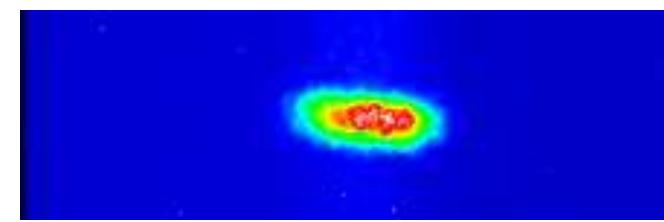




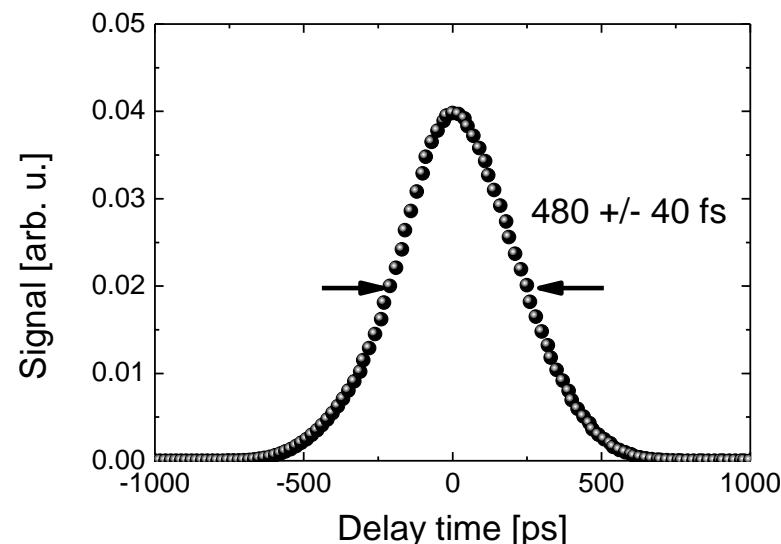
Streak camera



Without streak



With streak

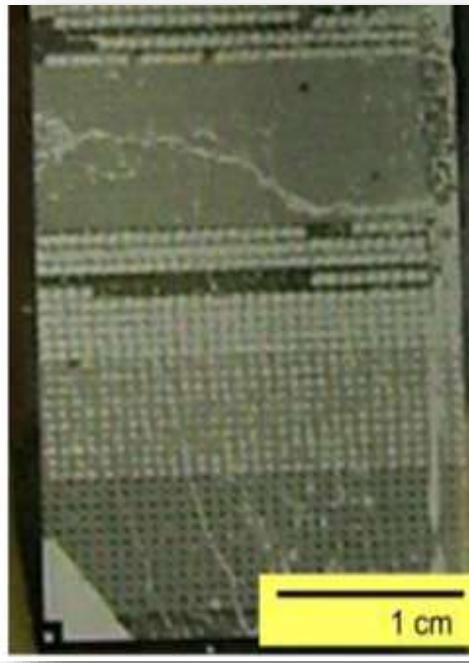


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Single-shot experiment

- Melting, Ablation and irreversible reactions
- Single or highly-oriented crystal sample
- Homogenous and large area sample



Julian Hirscht



Dongfang Zhang

Si nonthermal melting

PRL 100, 155504 (2008)

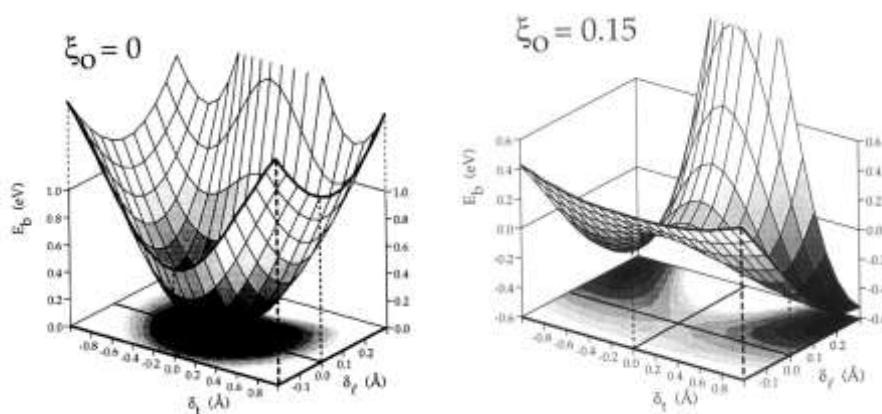
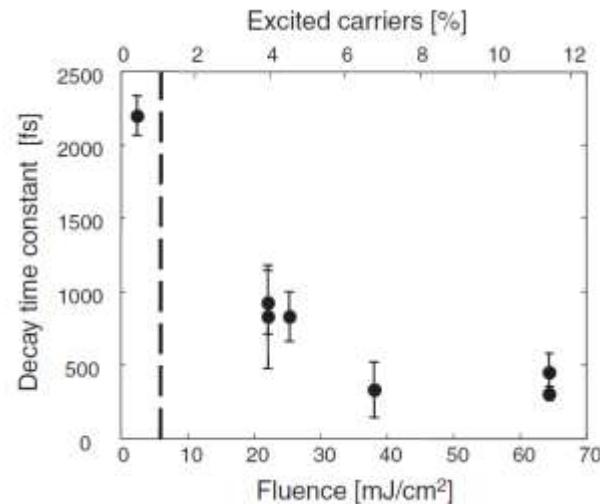
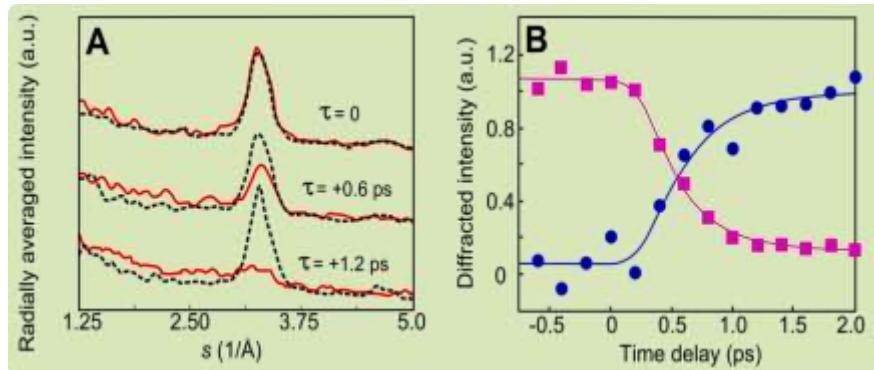
PHYSICAL REVIEW LETTERS

week ending
18 APRIL 2008



Electronically Driven Structure Changes of Si Captured by Femtosecond Electron Diffraction

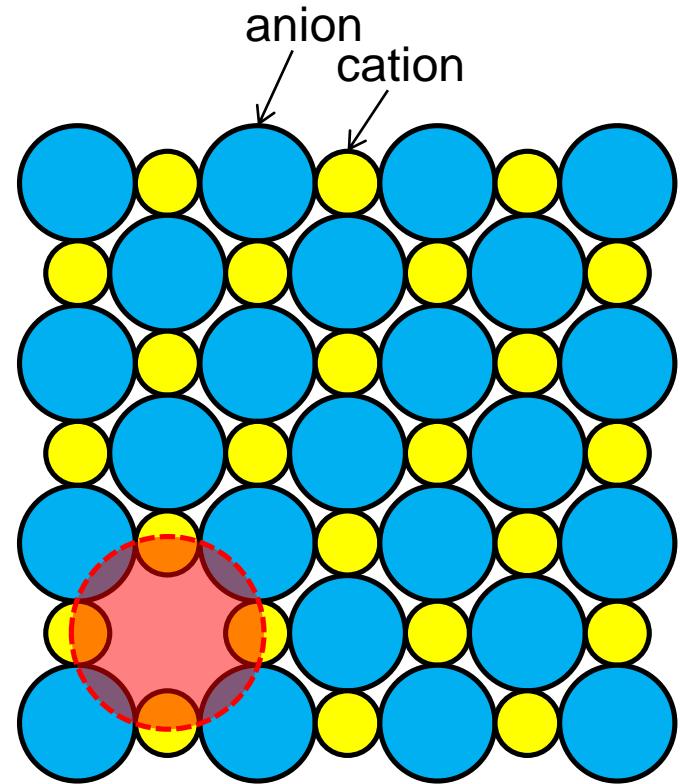
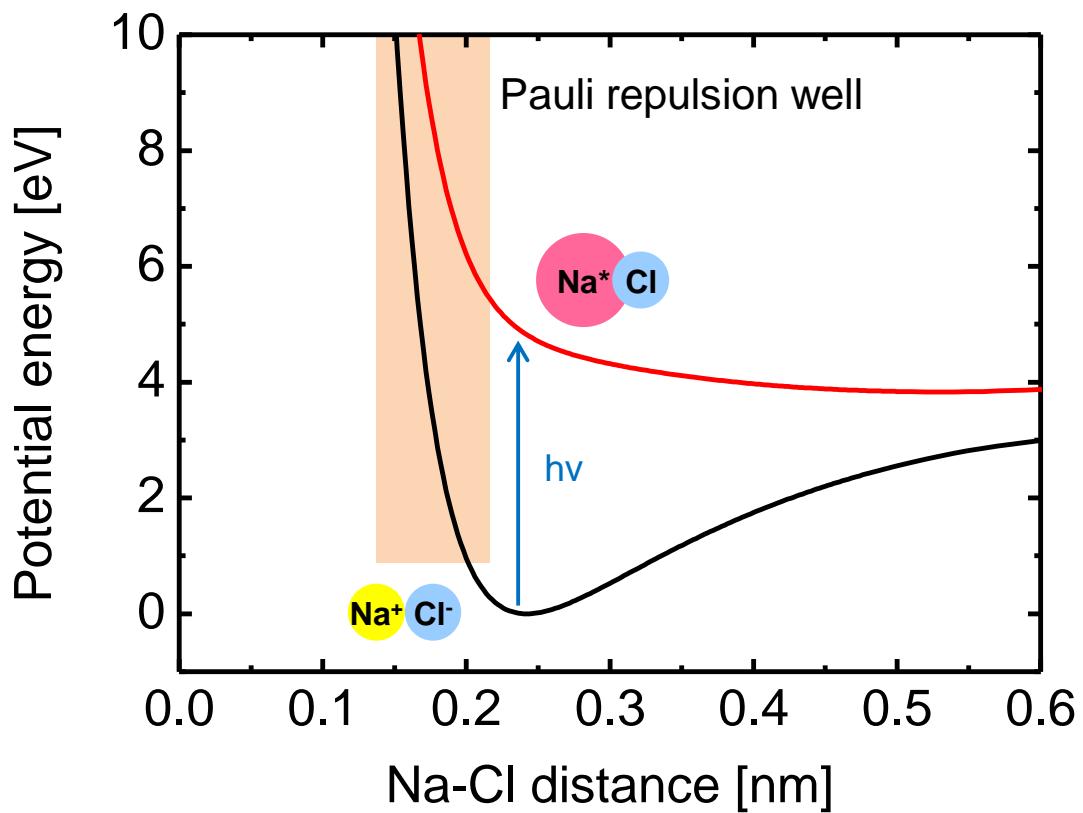
Maher Harb,¹ Ralph Ernstorfer,¹ Christoph T. Hebeisen,¹ Germán Sciaiani,¹ Wein Peng,² Thibault Dartigalongue,¹ Mark A. Eriksson,² Max G. Lagally,² Sergei G. Kruglik,¹ and R. J. Dwayne Miller^{1,*}



Nonthermal melting in Si !

P. Stampfli et al. Phys. Rev. B **49**, 7299 (1994)

Strong localized force in alkali halides



Self-trapped exciton, color center formation

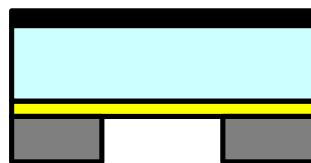
Sample preparation – KI thin crystals

Self standing SiN (30 nm) mesh by chemical etching process

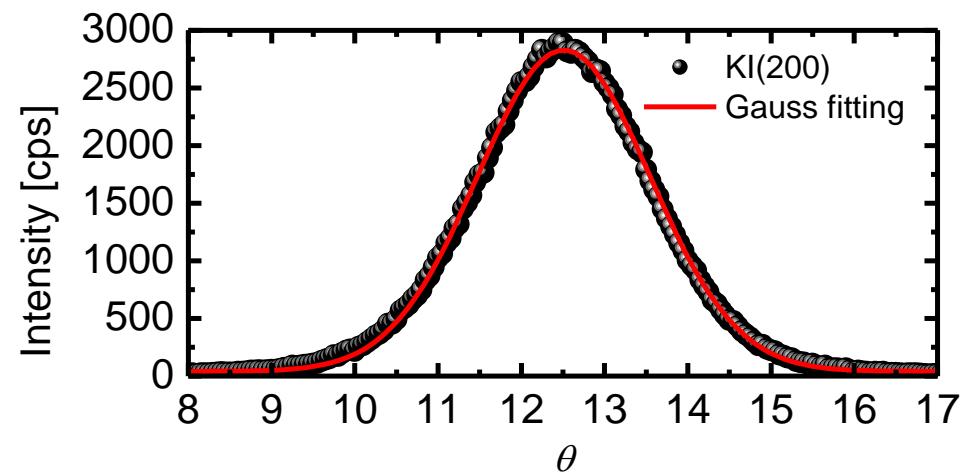
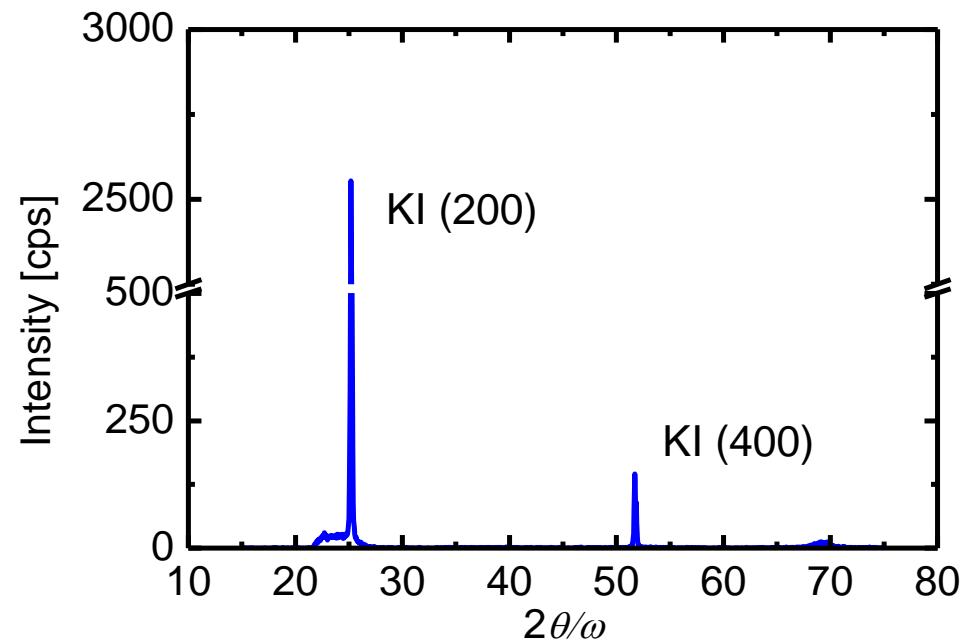
Pre-annealed (400 degrees)

Thermal deposition of KI (50 nm)

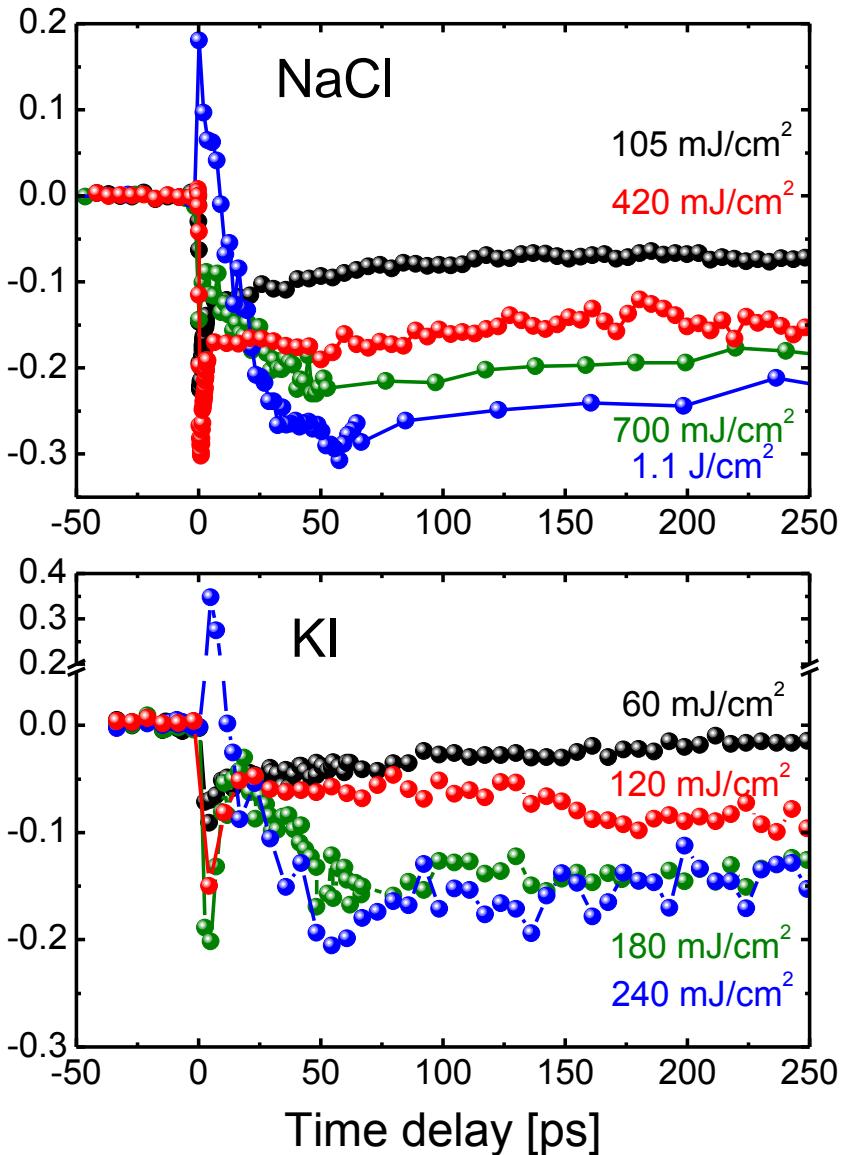
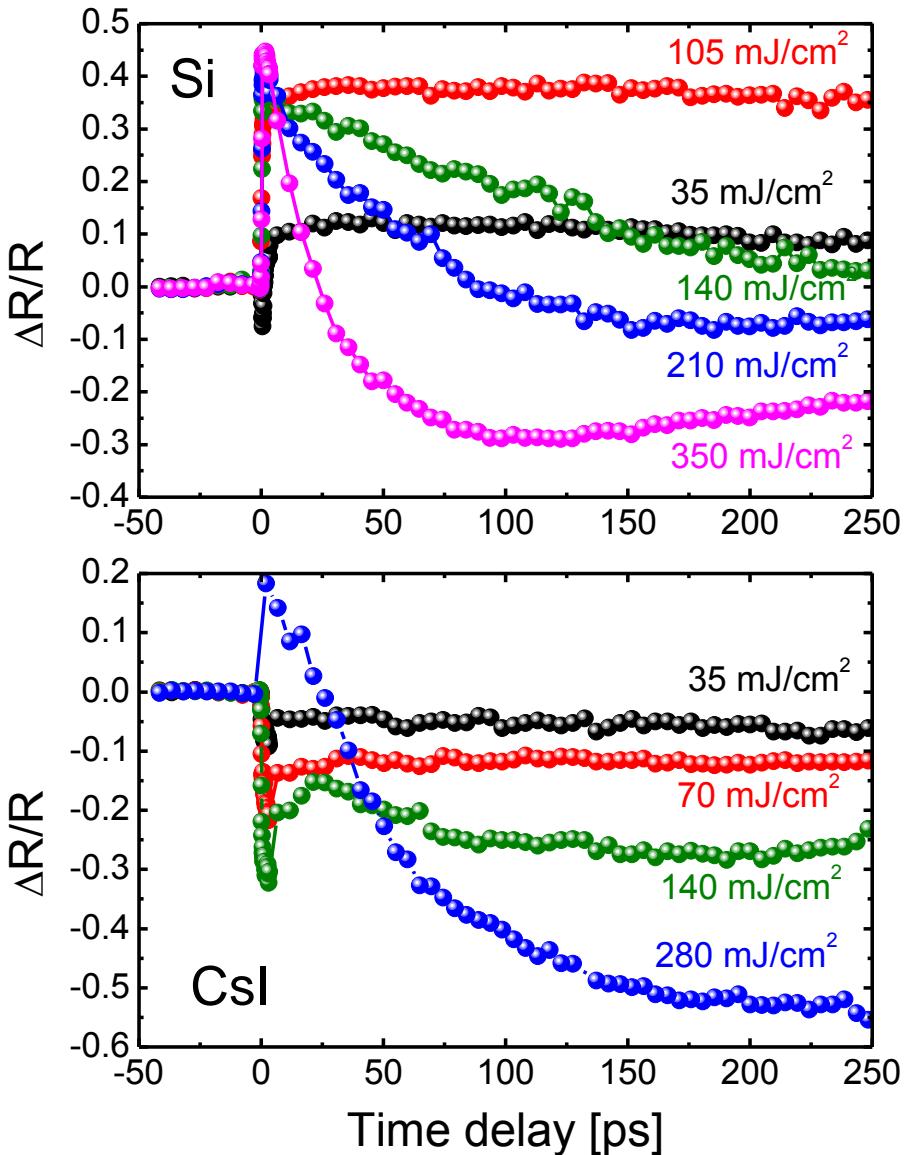
Coating with Carbon (4–5 nm)



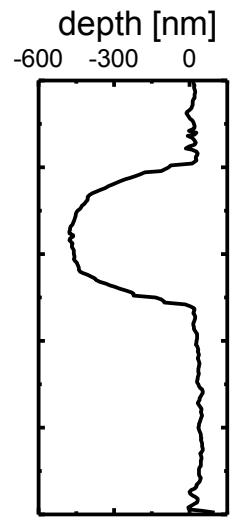
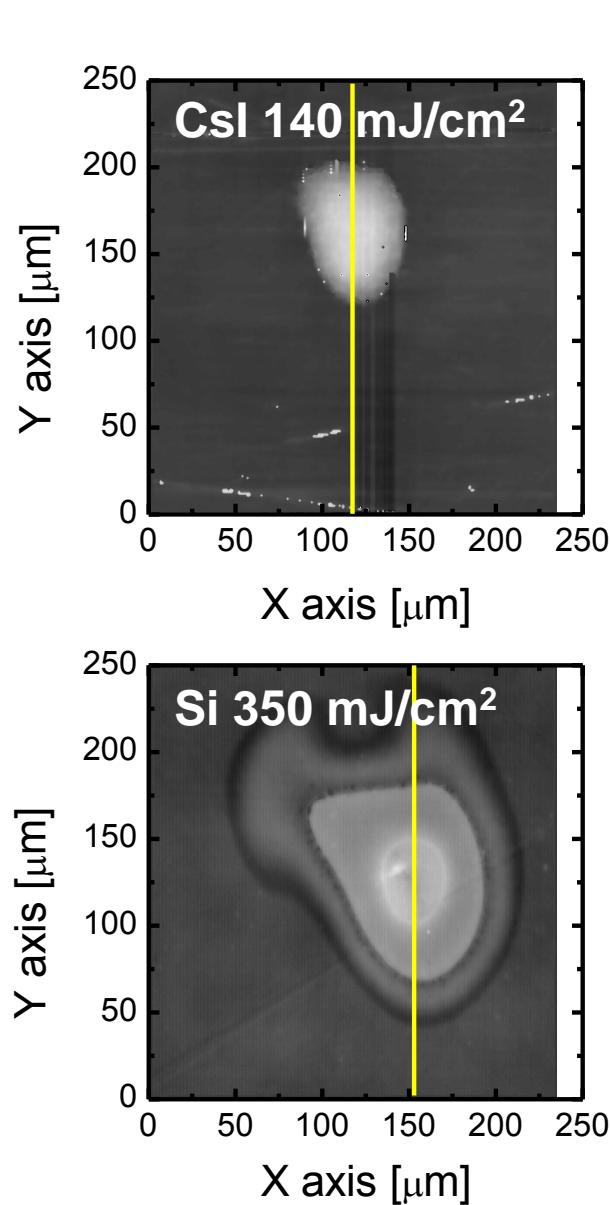
C (4–5 nm)
KI (50 nm)
SiN (30 nm)
Si substrate



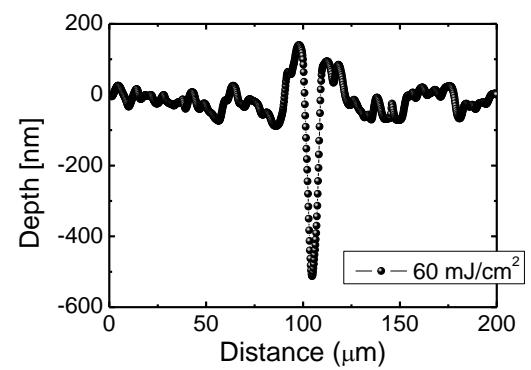
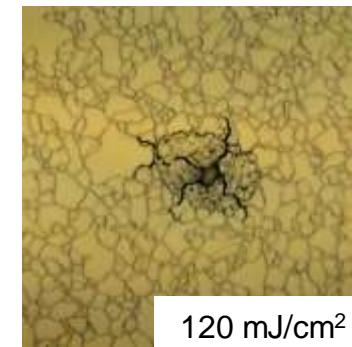
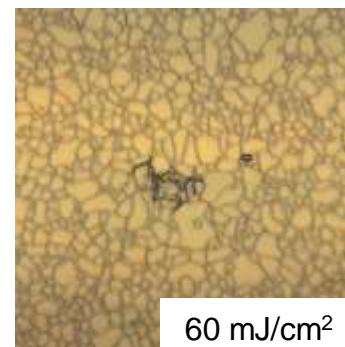
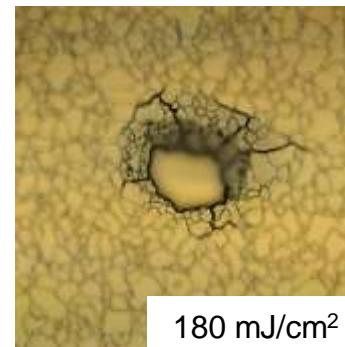
Optical studies



Sample surface after irradiation



KI

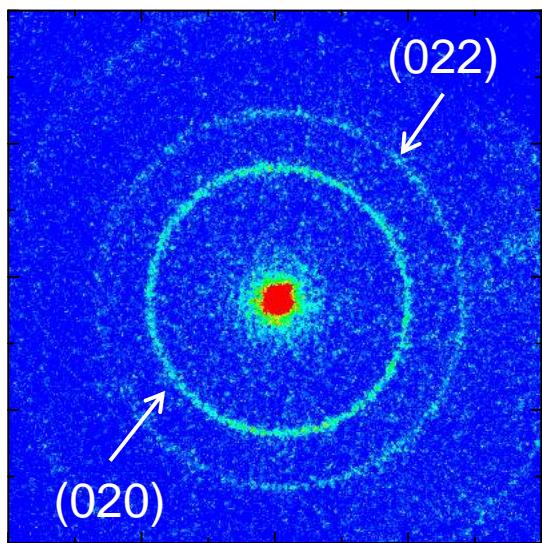


Micron deep crater formation in alkali halides with low laser fluence

Micron deep crater in alkali halides

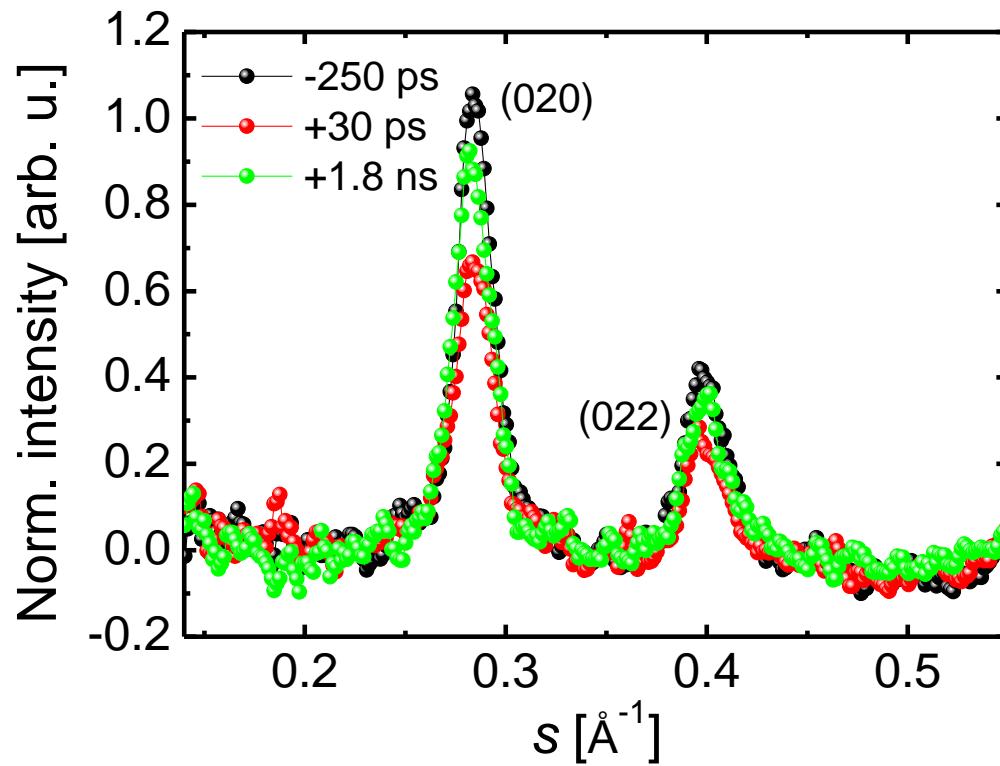
F	Depth (Si)	F	Depth (NaCl)
350 mJ/cm ²	26 nm	420 mJ/cm ²	970 nm
210 mJ/cm ²	16 nm	350 mJ/cm ²	950 nm
70 mJ/cm ²	9 nm	F	Depth (KI)
F	Depth (CsI)	180 mJ/cm ²	>2500 nm
280 mJ/cm ²	704 nm	120 mJ/cm ²	1400 nm
140 mJ/cm ²	472 nm	60 mJ/cm ²	500 nm
105 mJ/cm ²	418 nm		

Electron diffraction



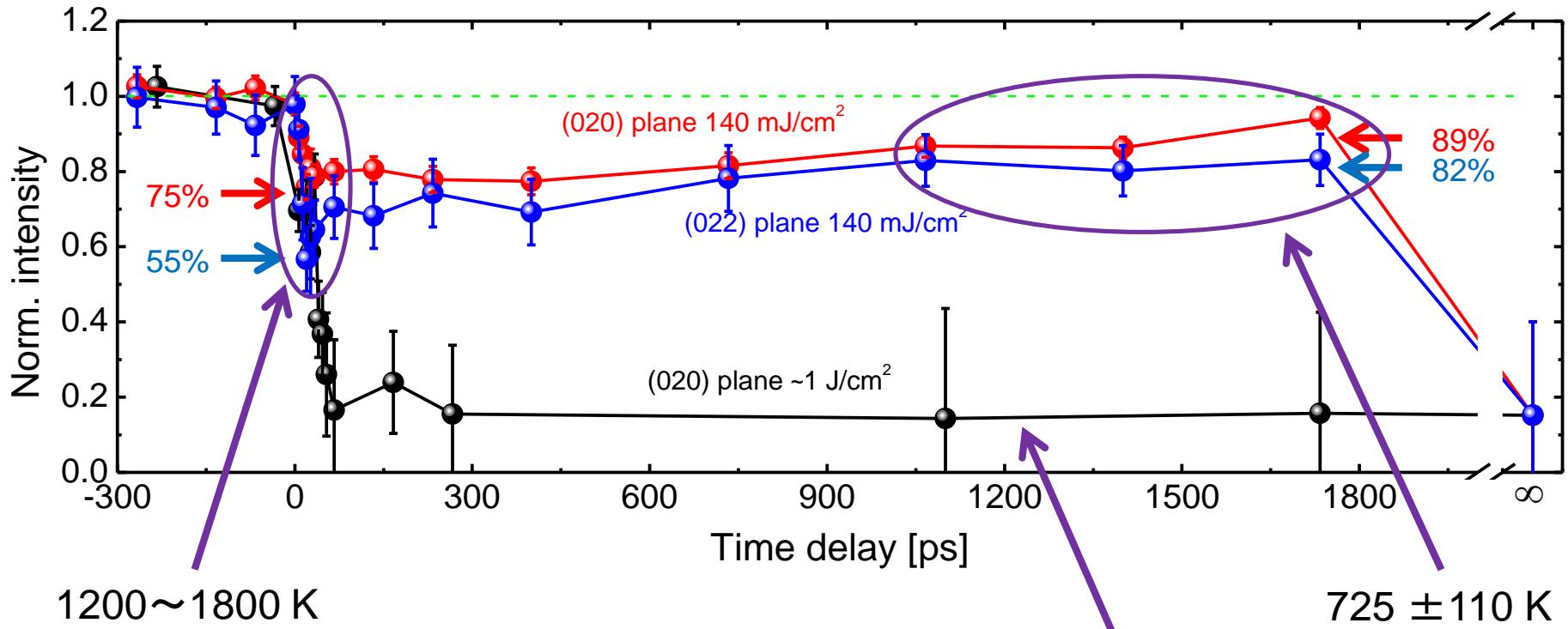
$F = 140 \text{ mJ/cm}^2$
Absorption = ~2%
Film thickness: 50 nm
2-photon absorption

Temperature raise
Excited halide center



~780 K (melting point 954 K)
~4%

Thermal? Plasma?

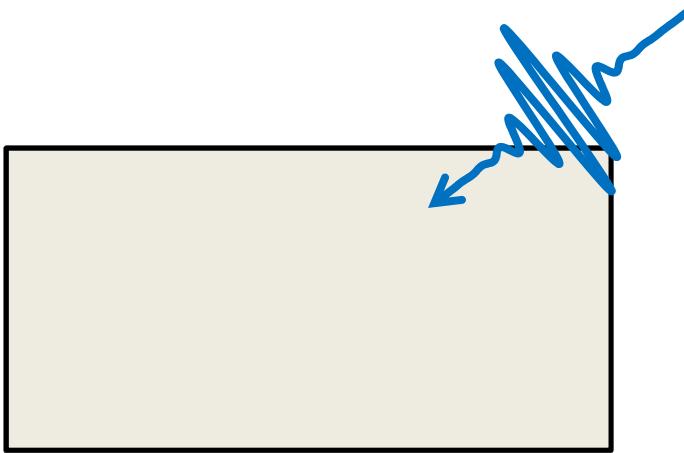


$$I = |F(\vec{K})|^2$$

$$F(\vec{K}) = G(\vec{K}) \sum_{j=1}^M f_j(\vec{K}) D_j(\vec{K}) \exp(2\pi i \vec{K} \cdot \langle \vec{r}_j \rangle)$$

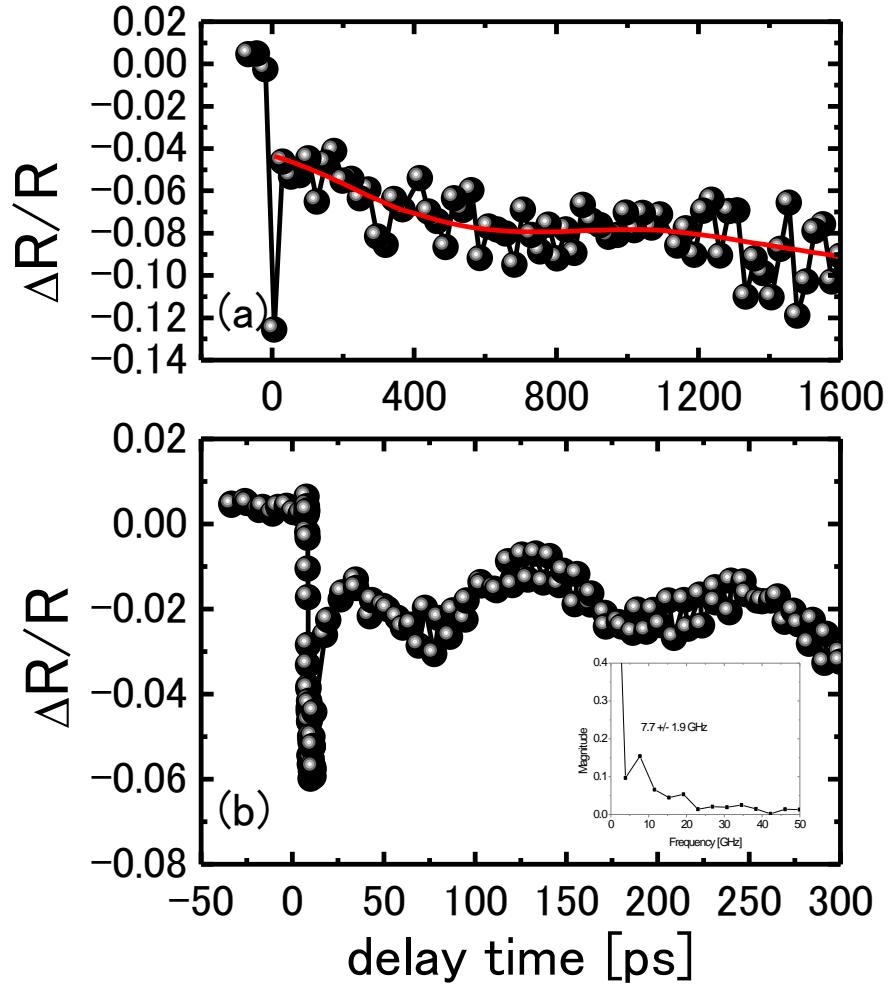
$$D_j = \exp(-K^2 B_j) = \exp(-8\pi^2 K^2 U_j) = \exp\left(\frac{8\pi^2 U_j \sin^2 \theta}{\lambda^2}\right)$$

Localized force in alkali halides



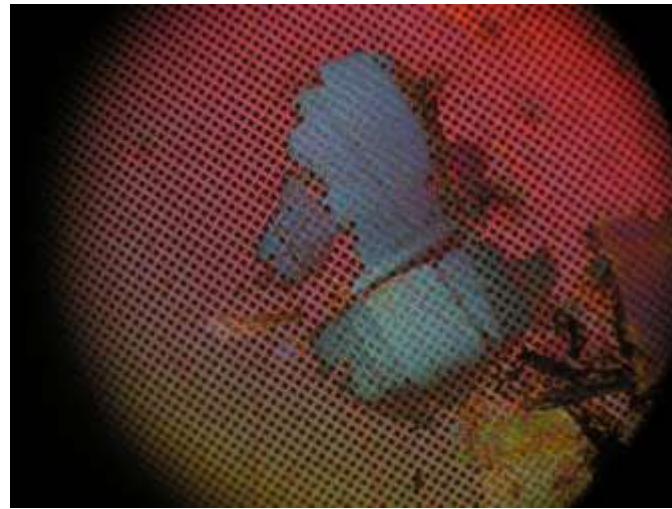
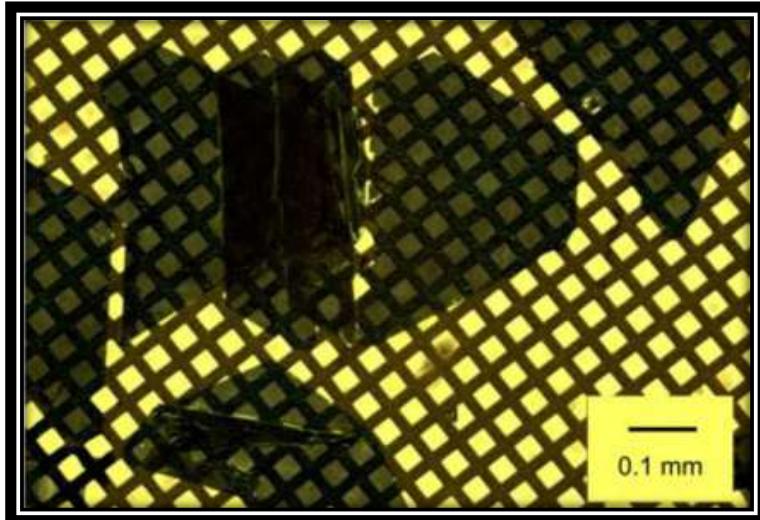
KI crystal
photoexcitation

These defects and disordered regions introduce strong electronic stress that leads to the expulsion of material.

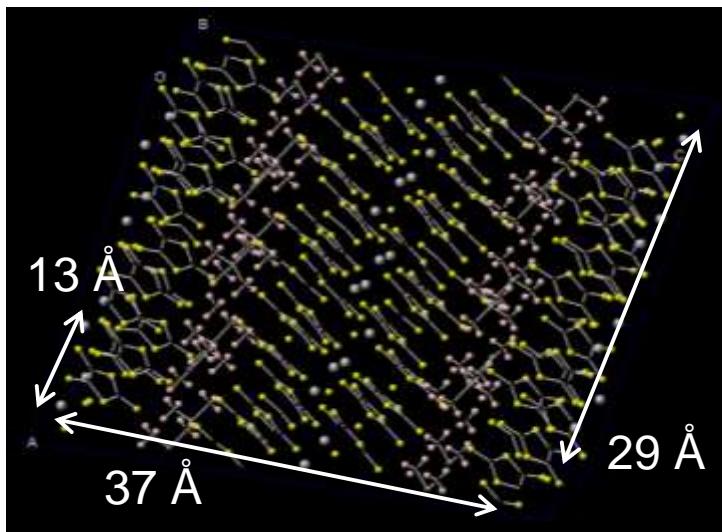


Multiple shot experiments

- Photoinduced repetitive reactions
- Single crystal
- Large structural modification
- Find a proper material



$\text{Me}_4\text{P}(\text{Pt}(\text{dmit})_2)_2$



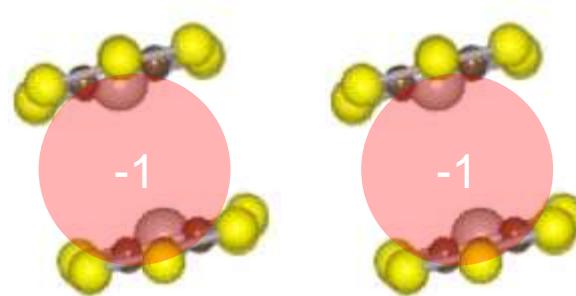
Stuart Hayes



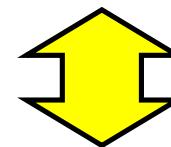
Tadahiko Ishikawa

Collaboration work
Miller Group, Max Planck Institute
Koshibara Group, Tokyo Institute of Technology
Kato Group, RIKEN

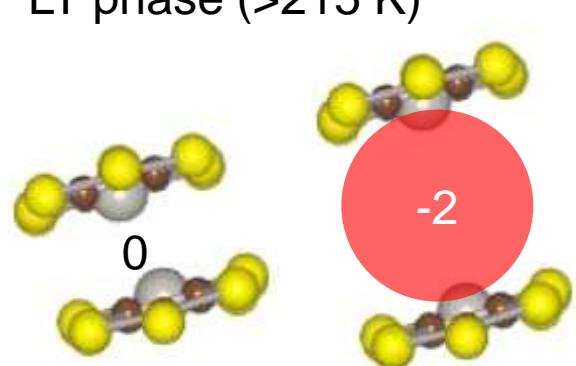
HT phase (>215 K)



Paramagnetic metal

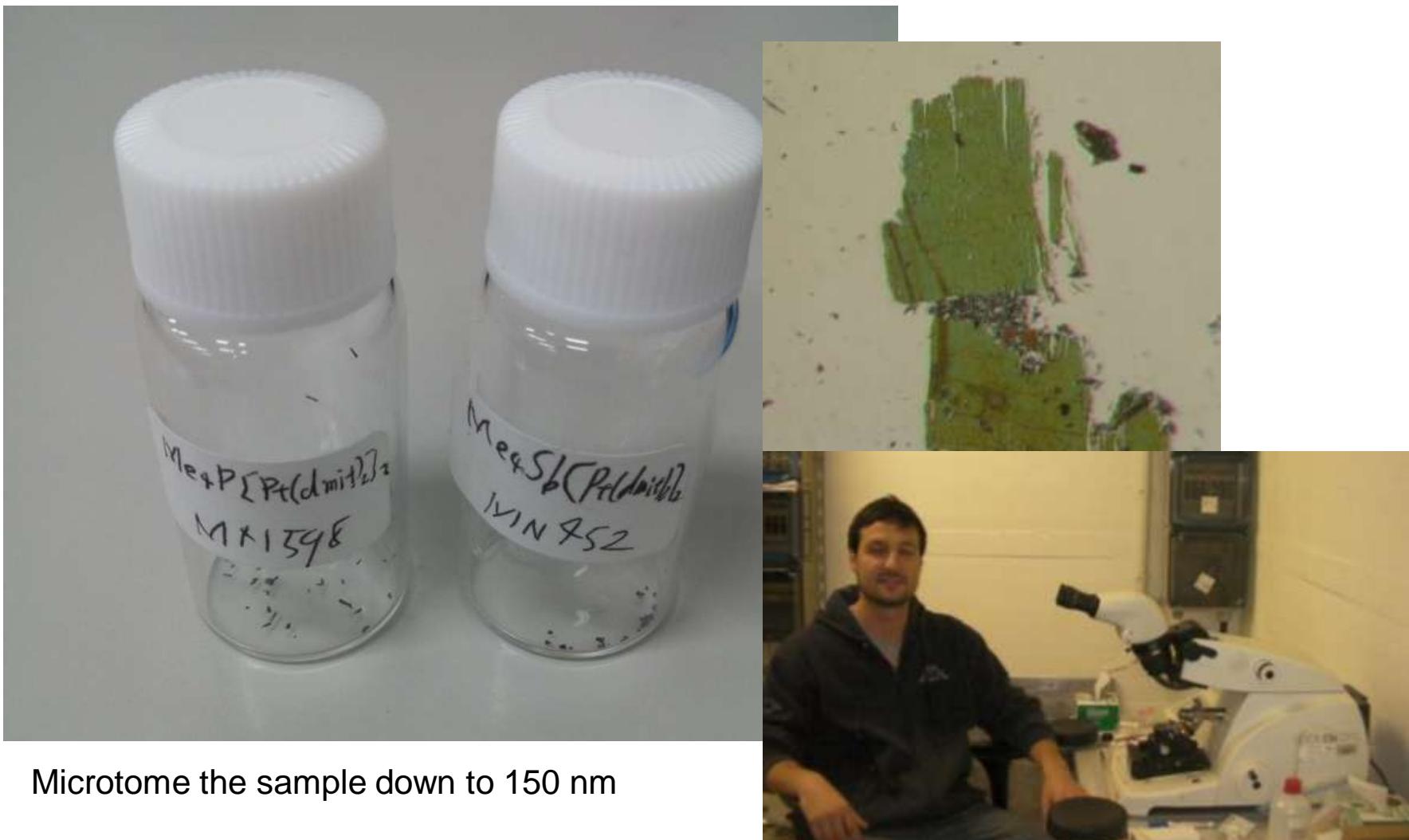


LT phase (>215 K)



Charge-ordered state
Non magnetic insulator

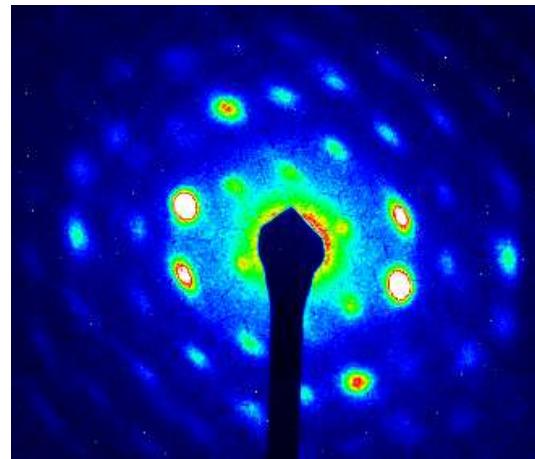
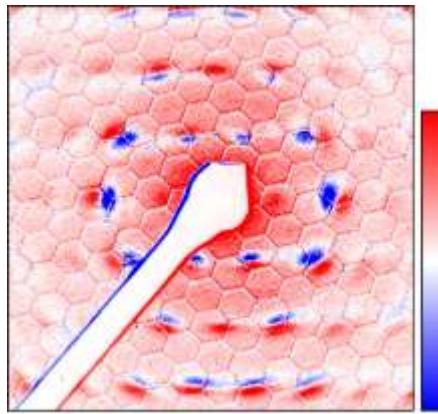
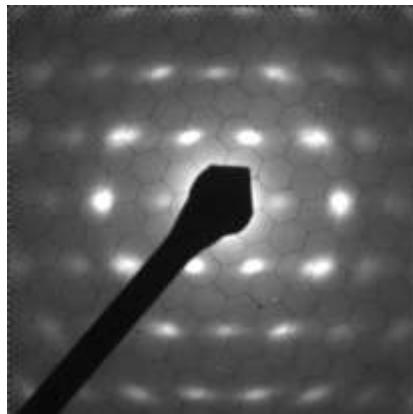
Sample preparation



Microtome the sample down to 150 nm

Sercan Keskin

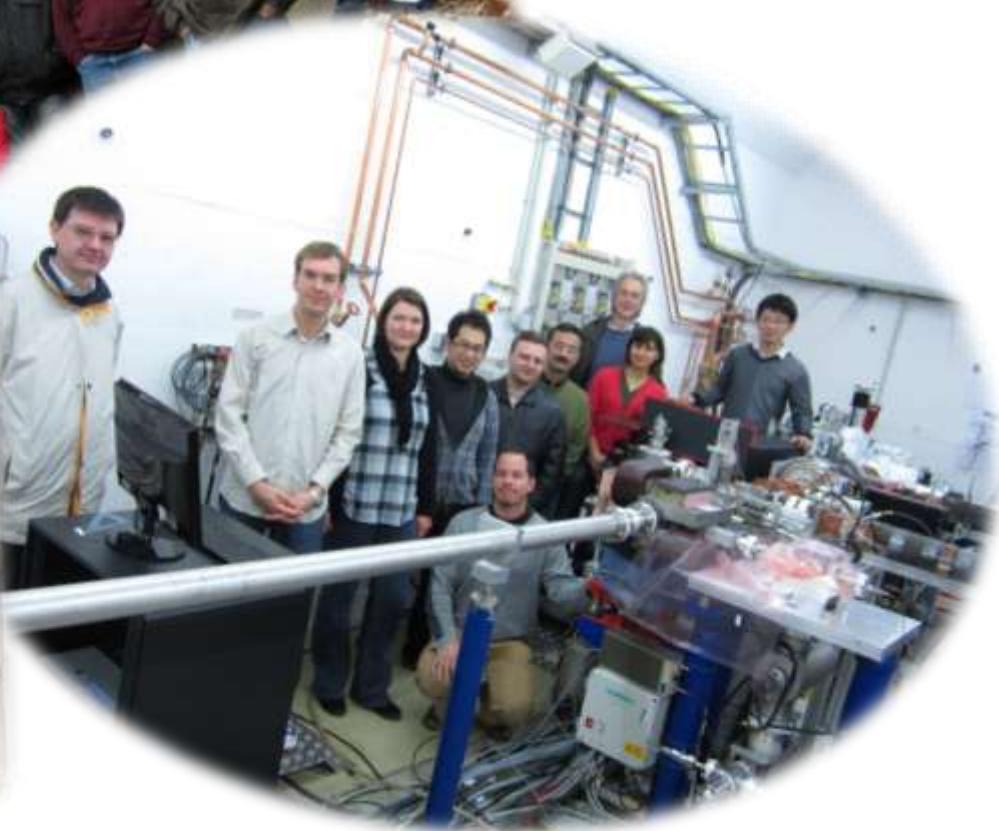
Coherent phonon oscillation



Crystal with large lattice parameters
→ We can go for protein crystals!?

We observed the coherent phonon oscillation...
We have not put the index yet...

Thank you for your attention!



Max-Planck-Institut für
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